



SEMITOP® 2

## IGBT Module

SK75GAL12T4

SK75GAR12T4

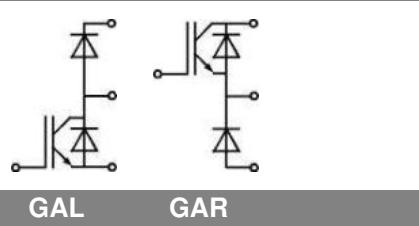
## Features

- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

## Typical Applications\*

## Remarks

- $V_{CE,sat}$ ,  $V_F$  = chip level value



Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200		V
$I_C$	$T_j = 175^\circ\text{C}$ $T_s = 25^\circ\text{C}$ $T_s = 70^\circ\text{C}$	80	A	
$I_{CRM}$	$I_{CRM} = 3 \times I_{Cnom}$	65	A	
$V_{GES}$		225	A	
$t_{psc}$	$V_{CC} = 800\text{ V}$ ; $V_{GE} \leq 15\text{ V}$ ; $T_j = 150^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		$\mu\text{s}$
<b>Inverse Diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$ $T_s = 25^\circ\text{C}$ $T_s = 70^\circ\text{C}$	20	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	16	A	
$I_{FSM}$	$t_p = 10\text{ ms}$ ; half sine wave $T_j = 150^\circ\text{C}$	45	A	
<b>Freewheeling Diode</b>				
$I_F$	$T_j = 175^\circ\text{C}$ $T_s = 25^\circ\text{C}$ $T_s = 70^\circ\text{C}$	70	A	
$I_{FRM}$	$I_{FRM} = 3 \times I_{Fnom}$	55	A	
$I_{FSM}$	$t_p = 10\text{ ms}$ ; half sine wave $T_j = 150^\circ\text{C}$	225	A	
<b>Module</b>				
$I_{t(RMS)}$				A
$T_{vj}$		-40 ... +175		$^\circ\text{C}$
$T_{stg}$		-40 ... +125		$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	min.	typ.	max.
<b>IGBT</b>				
$V_{GE(th)}$	$V_{GE} = V_{CE}$ , $I_C = 3\text{ mA}$	5	5,8	6,5
$I_{CES}$	$V_{GE} = 0\text{ V}$ , $V_{CE} = V_{CES}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		1,0	mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = 20\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$		600	nA
$V_{CEO}$	$T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	1,1	1,3	V
$r_{CE}$	$V_{GE} = 15\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 150^\circ\text{C}$	10	16	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 75\text{ A}$ , $V_{GE} = 15\text{ V}$ $T_j = 25^\circ\text{C}_{\text{chiplev.}}$ $T_j = 150^\circ\text{C}_{\text{chiplev.}}$	1,85	2,05	V
$C_{ies}$ $C_{oes}$ $C_{res}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ $f = 1\text{ MHz}$	0,29	0,235	nF
$Q_G$	$V_{GE} = -7\text{ V} \dots +15\text{ V}$	570		nC
$R_{Gint}$	$T_j = 25^\circ\text{C}$	10		$\Omega$
$t_{d(on)}$ $t_r$ $E_{on}$	$R_{Gon} = 15\text{ }\Omega$ $di/dt = 2000\text{ A}/\mu\text{s}$	50	60	ns
$t_{d(off)}$ $t_f$ $E_{off}$	$R_{Goff} = 15\text{ }\Omega$ $T_j = 150^\circ\text{C}$ $V_{GE} = -7 \dots +15\text{ V}$	13	500	mJ
$R_{th(j-s)}$	per IGBT	60	7	ns
		0,74		K/W



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## Features

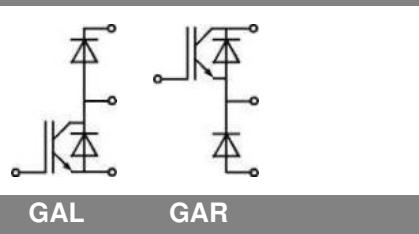
- One screw mounting module
- Trench4 IGBT technology
- CAL4 technology FWD

## Typical Applications\*

### Remarks

- $V_{CE,sat}$ ,  $V_F$  = chip level value

Characteristics		min.	typ.	max.	Units
Symbol	Conditions				
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 15 \text{ A}$ ; $V_{GE} = 0 \text{ V}$ $T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$ $T_j = 150 \text{ }^\circ\text{C}_{\text{chiplev.}}$		2,38 2,44	2,71 2,77	V
$V_{F0}$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 150 \text{ }^\circ\text{C}$		1,3 0,9	1,5 1,1	V
$r_F$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 150 \text{ }^\circ\text{C}$		72 102,8	80,7 111,6	mΩ
$I_{RRM}$ $Q_{rr}$ $E_{rr}$	$I_F = A$ $T_j = 150 \text{ }^\circ\text{C}$ $V_{CC} = 600 \text{ V}$				A μC mJ
$R_{th(j-s)D}$	per diode		2,34		K/W
<b>Freewheeling Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 75 \text{ A}$ ; $V_{GE} = 0 \text{ V}$ $T_j = 25 \text{ }^\circ\text{C}_{\text{chiplev.}}$ $T_j = 150 \text{ }^\circ\text{C}_{\text{chiplev.}}$		2,1 2,4	2,5 2,5	V
$V_{F0}$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 150 \text{ }^\circ\text{C}$		1,3 0,9	1,5 1,1	V
$r_F$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 150 \text{ }^\circ\text{C}$		12 16	13,3 17,3	V
$I_{RRM}$ $Q_{rr}$ $E_{rr}$	$I_F = 75 \text{ A}$ $di/dt = 2000 \text{ A/μs}$ $V_{CC} = 600 \text{ V}$		45 10 3		A μC mJ
$R_{th(j-s)FD}$	per diode		0,97		K/W
$M_s$	to heat sink			2,5	Nm
w			30		g
<b>Temperature sensor</b>					
$R_{100}$	$T_s = 100 \text{ }^\circ\text{C}$ ( $R_{25} = 5 \text{ k}\Omega$ )		493±5%		Ω



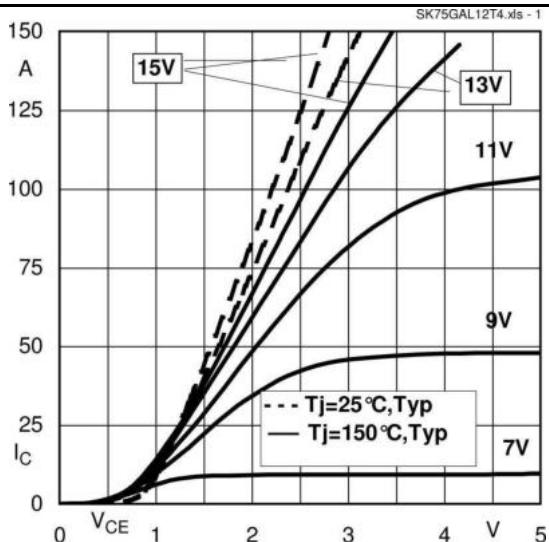


Fig. 1 Typ. output characteristic, inclusive  $R_{CC} + EE'$

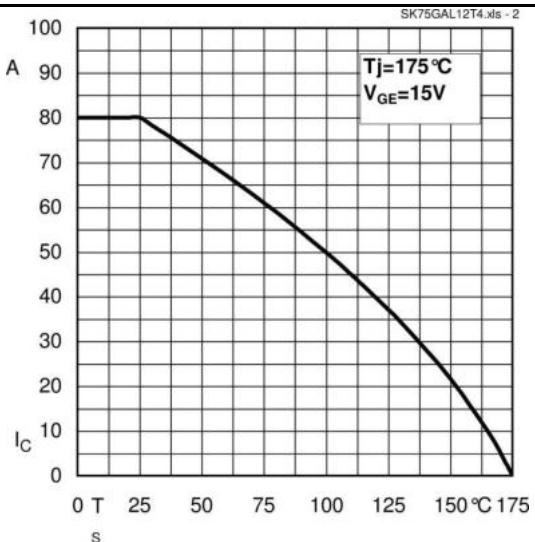


Fig. 2 Rated current vs. temperature  $I_C = f(T_s)$

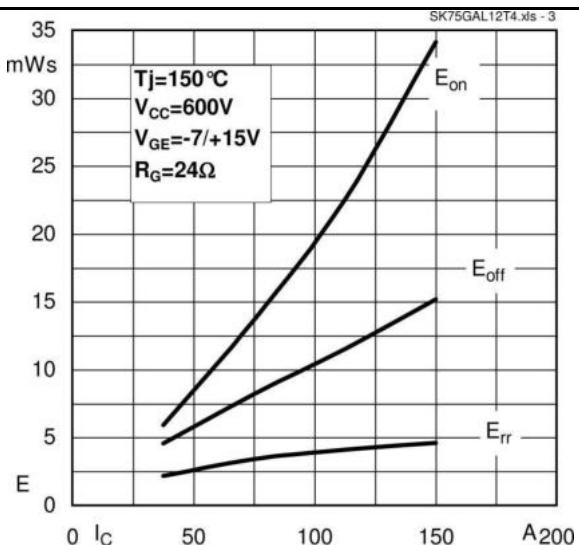


Fig. 3 Typ. turn-on /-off energy =  $f(I_C)$

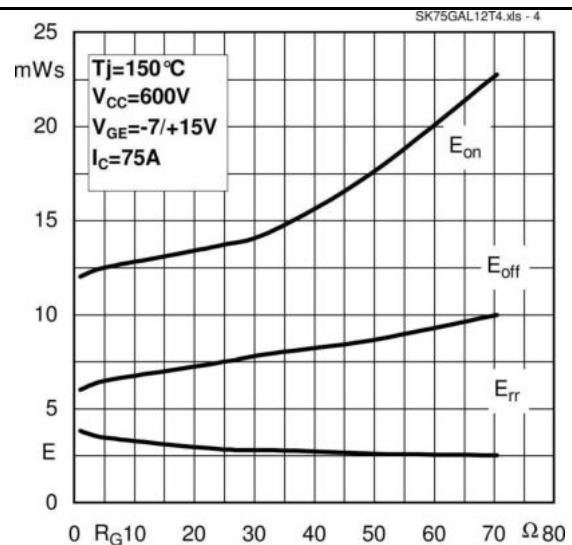


Fig. 4 Typ. turn-on /-off energy =  $f(R_G)$

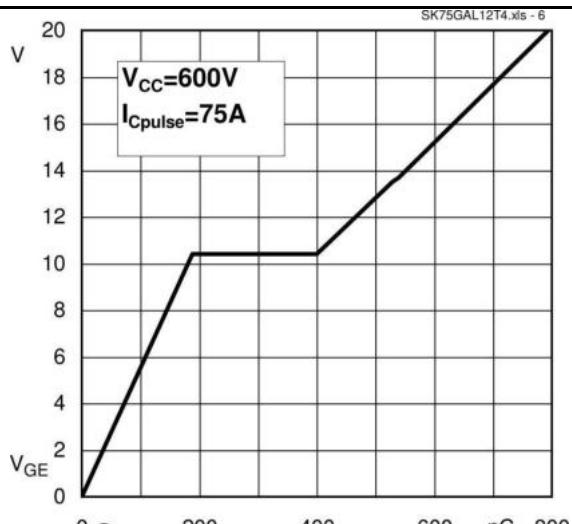


Fig. 6 Typ. gate charge characteristic

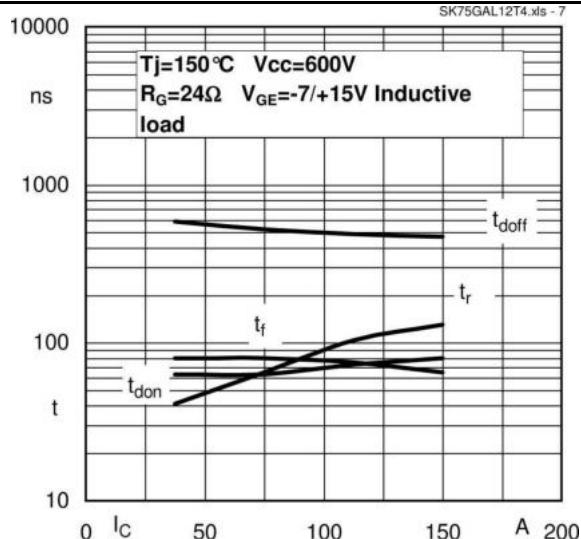


Fig. 7 Typ. switching times vs.  $I_C$

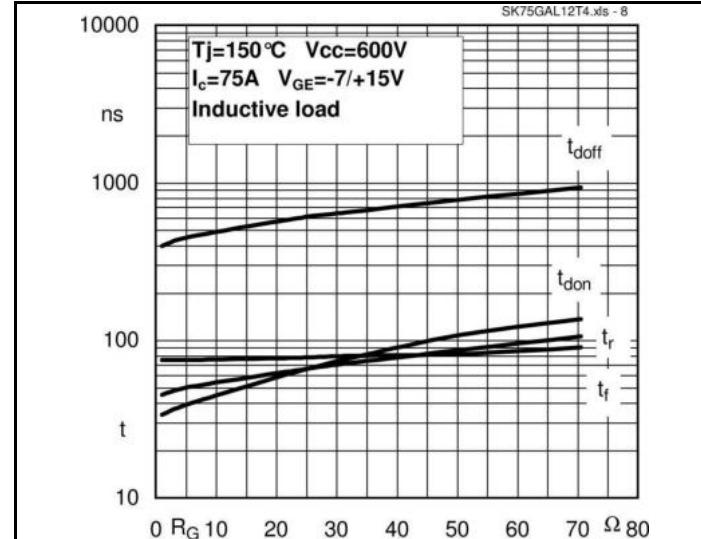
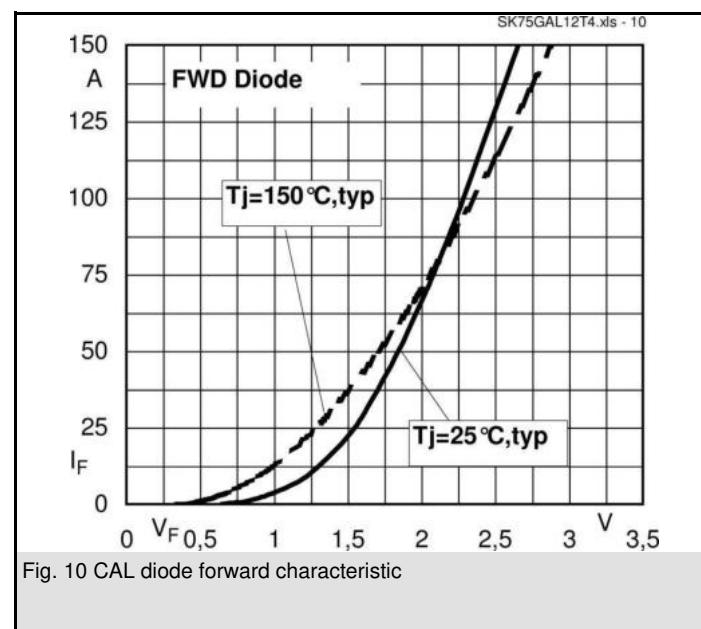
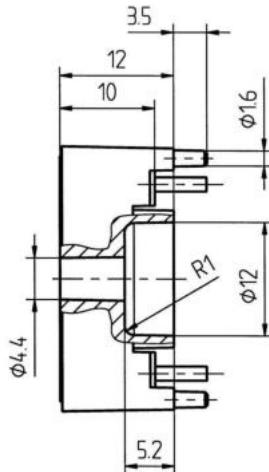
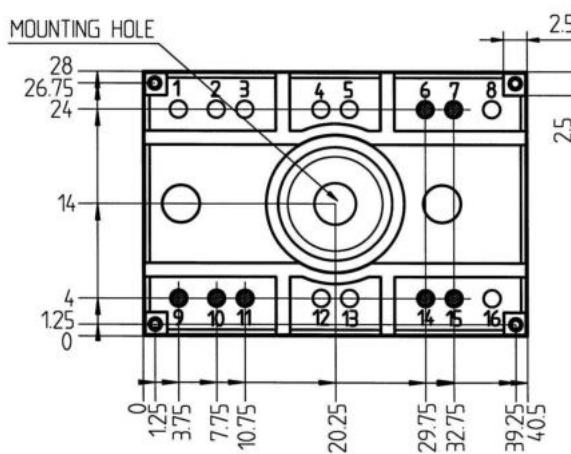
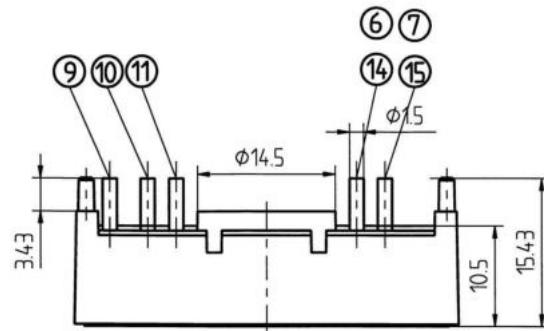
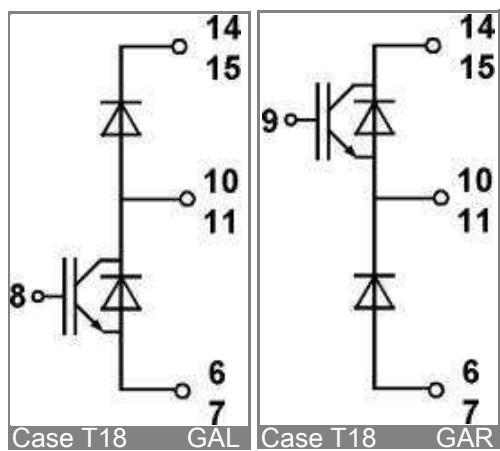


Fig. 8 Typ. switching times vs. gate resistor  $R_G$





Case T18 (Suggested hole diameter for the solder pins and mounting plastic pins: 2mm)



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, chapter IX.

#### \*IMPORTANT INFORMATION AND WARNINGS

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